



2N7002W

Preliminary

Power MOSFET

300m Amps, 60 Volts N-CHANNEL POWER MOSFET

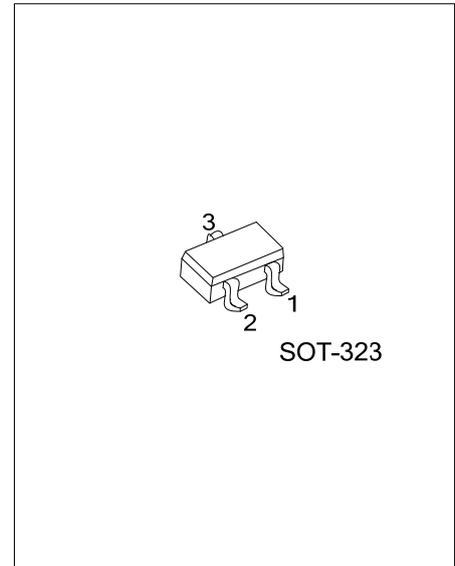
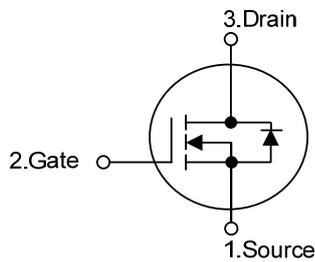
DESCRIPTION

The UTC **2N7002W** has been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. It can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. The product is particularly suited for low voltage, low current applications, such as small servo motor control, power MOSFET gate drivers, and other switching applications

FEATURES

- * High Density Cell Design for Low $R_{DS(ON)}$.
- * Voltage Controlled Small Signal Switch
- * Rugged and Reliable
- * High Saturation Current Capability

SYMBOL

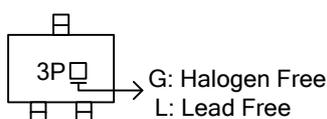


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N7002WL-AL3-R	2N7002WG-AL3-R	SOT-323	S	G	D	Tape Reel

2N7002WG-AL3-R	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AL3: SOT-323
	(3)Halogen Free	(3) G: Halogen Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted.)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage (R _{GS} ≤ 1MΩ)	V _{DGR}	60	V
Gate Source Voltage	V _{GSS}	±20	V
		±40	
Drain Current	I _D	300	mA
		800	
Power Dissipation	P _D	200	mW
Derated Above 25°C		1.6	mW/°C
Junction Temperature	T _J	+ 150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	625 (Note1)	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	60			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V			100	nA
		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS (Note2)						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D =250μA	1	2.1	2.5	V
Drain-Source On-Voltage	V _{DS(ON)}	V _{GS} = 10V, I _D =500mA		0.6	3.75	V
		V _{GS} = 5.0V, I _D =50mA		0.09	1.5	
On-State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} ≥2V _{DS(ON)}	500	2700		mA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =500mA, T _J =125°C			13.5	Ω
		V _{GS} =5.0V, I _D =50mA			7.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		20	50	pF
Output Capacitance	C _{OSS}			11	25	pF
Reverse Transfer Capacitance	C _{RSS}			4	5	pF
Turn-On Time	t _{ON}	V _{DD} =30V, R _L =150Ω I _D =200mA, V _{GS} =10V R _{GEN} =25Ω			20	nS
Turn-Off Time	t _{OFF}	V _{DD} =30V, R _L =25Ω I _D =200mA, V _{GS} =10V R _{GEN} =25Ω			20	nS
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =115mA (Note)		0.88	1.5	V
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				0.8	A
Maximum Continuous Drain-Source Diode Forward Current	I _S				115	mA

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2.0%

TEST CIRCUIT AND WAVEFORM

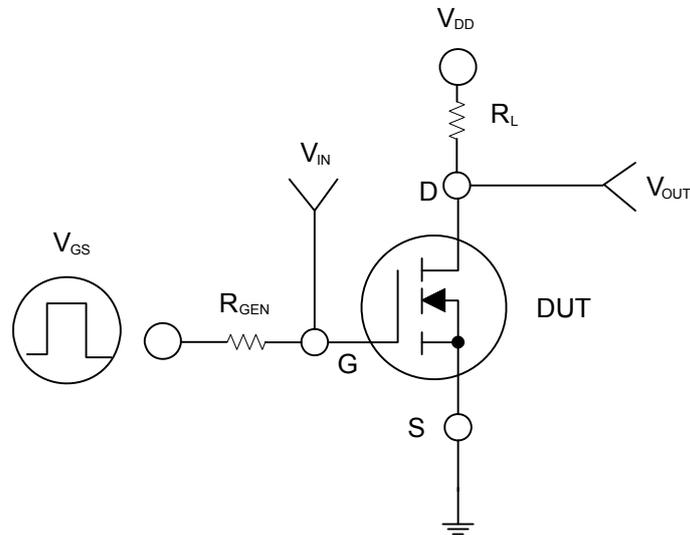


Figure 1

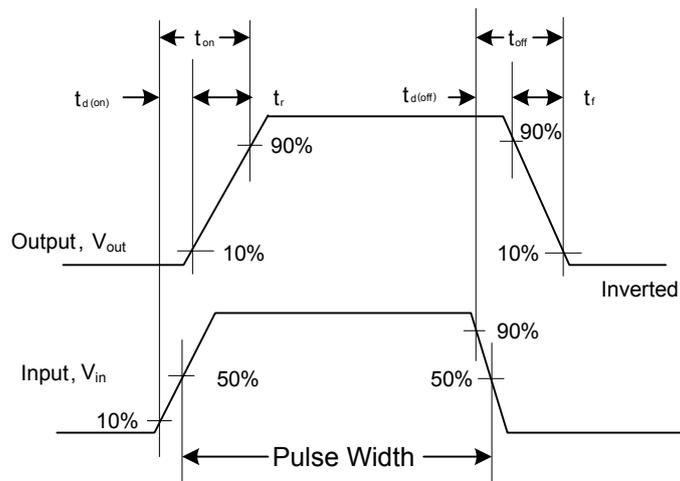


Figure 2. Switching Waveforms

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